## **International Journals:**

Area: Electronic Devices

- 1. Yeasir Arafat , Farseem M. Mohammedy , M. M. Shahidul Hassan, "Optical and Other Measurement Techniques of Carrier Lifetime in Semiconductors," International Journal of Optoelectronic Engineering, Vol. 2, No. 2, pp. 5-11, 2012.
- 2. M M Shahidul Hassan, Orchi Hassan and Md. Iqbal Bahar Chowdhury, "Effect of Majority Carrier Current on the Base Transit Time of A BJT," Journal of Electron Devices, Vol. 10, pp. 511-514, 2011.
- 3. M M Shahidul Hassan and Orchi Hassan, "Minority Carrier Profile and Storage Time of a Nonuniformly Doped n-Si Schottky Barrier Diode," Journal of Electron Devices, Vol. 11, pp. 609-615, 2011.
- 4. M M Shahidul Hassan and Orchi Hassan, "Depletion Layer of a Nonuniformly Doped Schottky barrier Diode," Journal of Electron Devices, Vol. 14, pp. 1151-1154, 2012.
- 5. M. M. Shahidul Hassan and Md. Waliullah Khan, "Base Transit Time Model Considering Field Dependent Mobility for BJTs Operating at High-Level Injection," IEEE Trans. On Electron Devices, Vol. 53, No. 10, pp. 2532-2539, Oct., 2006.
- 6. M. M. Shahidul Hassan, Ziaur Rahman Khan and Md. Touhidur Rahman, "Base Transit Time of a Bipolar Transistor considering Field Dependent Mobility," International Journal of Electronics, Vol. 93, No. 11, pp. 723-735 November 2006.
- 7.M. M. Shahidul Hassan, Touhidur Rahman and Md. Ziaur Rahman Khan, "Analytical model for base transit time of a bipolar transistor with Gaussian doped base," Solid-State Electron., Vol. 50, No. 3, pp. 327-332, 2006.
- 8. Md. Anwarul Abedin and Dr. M. M. Shahidul Hassan, "Base Transit Time Model of a Bipolar Junction Transistor Considering Kirk Effect," Journal of The Institution of Engineers, Singapore, Vol. 45, Issue 5, 2005.
- 9. Md. Anwarul, Abedin and M. M., Shahidul Hassan, Analytical base transit time model of uniformly doped base bipolar transistors considering Kirk effect, The Journal of the Institution of Engineers, Malaysia, vol. 66(3), 2005, pages 42-46.
- 10.Md. Z. R. and M.M.S. Hassan and T.Rahman and A. k. M. Ahsan, "Expression for Base Transit Time in Bipolar Transistors," Int. J. Electronics, Vol. 92, No. 4, pp. 215-229, April 2005.
- 11 M. M. Shahidul Hassan, A. H. M. A. Rahim, "Induced Base Transit Time of an Epitaxial n<sup>+</sup>pn<sup>-</sup>n<sup>+</sup> Bipolar Transistor in Saturation," Solid-State Electronics, Vol. 47, No.6, pp. 943-950, 2003.
- 12.M. M. Shahidul Hassan, "Base Transit Time of an Epitaxial n<sup>+</sup>pn<sup>-</sup>n<sup>+</sup> Bipolar Transistor Considering Kirk Effect," Int. J. Microelectronics and Reliability, Vol. 43, No. 2, pp. 327-332, 2003.
- 13.M. M. Shahidul Hassan and S. Hasibul Majid, "Electrical Characteristics of an Epitaxial Schottky Barrier Diode," International Journal of Electronics, Vol. 88, No. 9, pp. 957-967, 2001
- 14. M. M. Shahidul Hassan and A. H. Khondoker, "New Expression for Base Transit Time in a Bipolar Transistor for all levels of Injection, "Microelectronics and Reliability, Vol. 41, No. 1, pp. 137-140, 2001.

- 15. M. M. Shahidul Hassan, "Analytical Base Transit Time of Integrated Bipolar Transistors in Quasi-saturation and Hard-saturation," IEE Proc.-Circuits, Devices and Systems, 147, No. 2, pp. 129-132, 2000.
- 16.M. M. Shahidul Hassan, "Characteristics of Epitaxial Schottky Barrier Diode for all Levels of Injection," Solid-State Electronics, Vol. 44, No. 6, pp.1111-1116, 2000.
- 17. M. M. Shahidul Hassan, "Modelling of Lightly Doped Collector of a Bipolar Transistor Operating in Quasi-saturation Region," Int. Journal of Electronics, Vol.86, No.1, pp. 1-14, 1999. 18.M. M. Shahidul Hassan and M. A. Choudhury, "New Formulation of the Collector Current and Current Gain Relations for Design Purposes of Power Transistors Switches," IEE Proc. Circuits, Devices and Systems, Vol. 142, No.2, pp. 113-119, 1995.
- 19.M. M. Shahidul Hassan and Md. Aynal Haque, "Evaluation of Optimal Collector Parameters of a Transistor with Burried Layer," Int. J. Electronics, Vol. 75, No. 3, pp. 437-440, 1993.
- 20. M. M. Shahidul Hassan, Golam Rasul Chowdhury and Zahirul Alam, "Breakdown Voltage of High-Voltage Bipolar Transistors," Solid-State Electronics, Vol. 34, No. 10, pp. 1109-1111, 1991
- 21. M. M. Shahidul Hassan and H. Domingos, "Design of Optimal Values of Epitaxial Bipolar Transistor Switches," Int. J. Electronics (IJE), Vol. 71, No. 5, pp. 745-755, 1991.
- 22.M. M. Shahidul Hassan and A. Habib, "Avalanche Breakdown Voltages of Linearly Graded Si Junctions," IJE Vol.71, No.3, pp. 403- 409, 1991.
- 23.M.M. Shahidul Hassan and H. Domingos, "Breakdown Voltages of Base-Collector Junctions of Medium- and Low -Voltage Graded Collector Transistors," Int. J. Electronics, Vol. 70, No. 1, pp. 69-75, 1991.
- 24.M. M. Shahidul Hassan and H. Domingos, "Breakdown Voltages of Base Collector Junctions of High-Voltage Power Transistors with Graded Collectors," Int. J. Electronics, Vol. 70, No. 1, pp. 77-83, 1991.
- 25.M. M. Shahidul Hassan and H. Domingos, "Control of Current Mode Second Breakdown in Transistors through Use of Double-Graded Collectors," Solid-State Electronics, Vol. 33, No. 10, pp. 1217-1221, 1991.
- 26. M. M. Shahidul Hassan and H. Domingos, "Calculation of Avalanche Breakdown Voltages of Abrupt Si P-N Junctions," Int. J. Electronics, Vol. 68, No. 4, pp. 533-537, 1990.
- 27. M. M. Shahidul Hassan and H. Domingos, "Estimate of Peak Voltage for Triggering Current Mode Second Breakdown of BJTs during Inductive Turnoff," Int. J. Electronics, Vol. 66, No. 3, pp. 361-369, 1989.
- 28. M. M. Shahidul Hassan and H. Domingos, "Estimate of Minimum Current for Inducing Current Mode Second Breakdown in Reverse Biased Epitaxial Bipolar Transistors," Int. J. Electronics, Vol. 66, No. 3, pp. 371-377, 1989.
- 29. M. M. Shahidul Hassan and H. Domingos, "Increase of Critical Current Density and Voltage for Triggering Avalanche Injection through Use of Graded Collector Doping," Int. J. Microelectronics and Reliability, Vol. 29, No 2, pp. 217-226, 1989.

## **National Journals**

## **Area: Electronic Devices**

- 1. Yeasir Arafat, Md. Jannatul Ferdous and M. M. Shahidul Hassan, "Effect of Temperature on the Fill Factor of a Heterojunction (CIGS) Solar Cell," JIEB, Vol. EE 38, No. 11, Dec.2012.
- 2. M M Shahidul Hassan, Orchi Hassan and Md. Azharul Haque, "Minority Carrier Profile and Storage Time of a Schottky Barrier Diode for All levels of injection," JIEB, Vol 37, No 2, pp. 15-21, 2011.
- 3. Md.Waliullah Khan Nomani and M. M. Shahidul Hassan, "A New model of base transit time for BJTs operating at high level of injection," JIEB, 2006.
- 4. M. M. Shahidul Hassan and M. Azharul Haque, "Base Transit Time of a High Speed NPN Transistor Considering Hole current," JIEB, Vol. EE 33, No. 1& II, pp. 120-124, Decber 2006.
- 5. Touhidur Rahman, Md. Ziaur Rahman Khan, Hassan MMS, "Base Transit Time of a Bipolar Transistor with Gaussian Base Doping Profile", IEB Journal of Electrical Engineering, Vol. EE 31, No. I & II), pp. 6 9, Dec 2004
- 6.Md. Aynal Haque and M. M. Shahidul Hassan, "Design of a Graded Collector of High Voltage Bipolar Transistors," JIEB, Vol. EE 27, No. 1, pp. 57-61, 1999.
- 7. Mohammad Zahangir Kabir and M. M. Shahidul Hassan, "Determination of Excited Energy States of Submicron Inversion MOSFETs by Variational Method," JIEB, Vol. EE24, pp. 61-67, 1996.
- 8.Md. Nasim Ahmed Dewan and M. M. Shahidul Hassan, "Modeling of Bipolar Junction Transistor Thermal Effects," JIEB, Vol. EE24, pp.19-26, 1996.
- 9.M. M. Shahidul Hassan and Md. Kamrul Hassan, "Dependence of Second Breakdown on Load Inductance and Reverse Base Drive," JIEB, Vol. EE23, pp. 29-36, 1995.
- 10. Md. Tanvir Quddus and M. M. Shahidul Hassan, "Analytical Modelling of Breakdown in Short Channel MOSFET's", JIEB, Vol. EE 23, pp. 1-8, 1995.
- 11. M. M. Shahidul Hassan, "Optimum Design of Darlington Power Transistor Switches," JIEB, Vol. 22, No. 1, pp. 215-222, 1994.
- 12. M. M. Shahidul Hassan and G.. R. Choudhury, "Effect of Doping on Efficiency of MIS Inversion Layer Solar Cells," JIEB, Vol. 20, pp. 33-39, 1992.
- 13.M. M. Shahidul Hassan and M. A. Choudhury, "A Model for Designing Power Transistor Switches Driven in Hard Saturation in its On-State," JIEB, Vol. 20, No. 3, pp. 29-35, 1992.
- 14. M. M. Shahidul Hassan, M. M. Rahman and S. M. Sohel Imtiaz, "An Analytical Model for Current Mode Second Breakdown in Epitaxial Bipolar Transistor under Open-Base Operating Conditions," JIEB, Vol. 18, pp. 23-34,1990.
- 15.M. M. Shahidul Hassan and M. A. Choudhury, "Effect of Low-High junction on the Current-Gain Product of High-Voltage Power Transistors Operating in Saturation Region," JIEBS, Vol. 3, pp. 19-22, 1993.
- 16.M. M. Shahidul Hassan, "Evaluation of Optimal Values of Double-Graded Collector Parameters of High-Voltage Transistors," JBES, Vol. 2, No. 1, pp. 37-40, 1992.
- 17. M. M. Shahidul Hassan and M. Sohel Imtiaz, "Current- Voltage Characteristics of a Reverse Biased Transistor Driven in Current Mode Second Breakdown," JBES, Vol. 1, No. 1, pp. 17-23, 1991.
- 18. M. M. Shahidul Hassan and Golam Rasul Chowdhury, "Doping Dependence of Current Mode Second Breakdown in Epitaxial Bipolar Transistor," JBES, Vol. 1, No. 1, pp. 27-30, 1991.

## **International Journals**

**Area: Higher Education** 

1. M. M. Shahidul Hassan and Omiya Hassan, "The Importance of Changing the Traditional Mode of Higher Education in Bangladesh: Creating Huge Job Opportunities for Home and Abroad,"International Journal of Humanities and Social Sciences, Vol : 13, No:6, 2019.

- 2. M. M. Shahidul Hassan, "Revamping Higher Education in Bangladesh," International Journal of Management and Applied Science (IJMAS), pp. 53-55, Volume-2, Issue-12, 2017.
- 3. M M Shahidul Hassan, "On Challenges of Implementing Outcome Based Engineering Education in Universities in Bangladesh", JPU, 20-22 Dec. 2012, pp. 362 364